Structural and Compositional Analysis Of Single Crystal Niobium

via Transmission Electron Microscopy (TEM) And Secondary Ion Mass Spectrometry (STEM)



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FIB Prepared TEM Cross Sections for Jefferson Labs Nb (100), (110), (111)

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Overview

- Samples sputter coated with 60nm of Au-Pd to prevent surface damage from Ga Focused Ion Beam (FIB)
- Samples additionally coated by in situ deposition with 2µm of W in region of analysis
- FIB preparation performed with an Hitachi FB-2100 Focused Ion Beam System
- TEM micrographs captured with a Gatan Digital Camera on a JEOL JEM2010F High Resolution TEM/STEM
- Oxide Nb(100) ~4.9nm, Nb(110) ~8.3nm, Nb(111) ~7.5nm



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TEM Summary

Oxide Thickness measurements:

Nb(100) ~4.9nm, Nb(110) ~8.3nm, Nb(111) ~7.5nm

Sub-oxides? More investigation needed



SIMS: Secondary Ion Mass Spectrometry

SIMS Analysis of H, C, O in single crystal Nb

with 100, 110, 111 orientationsbefore and after anneals

Fred Stevie Dieter Griffis

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Secondary Ion Mass Spectrometry (SIMS)

- Ion bombardment of surface
- Sputtered species analyzed
- Detection of mass resolved secondary ions
- Good sensitivity (ppm) and nm depth resolution

•Analyzed region is near surface only!

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SIMS Process



Primary ion penetrates surface, energy lost through collision cascade, primary ion implanted into solid, secondary particles (including ions) leave surface at low energy

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CAMECA IMS-6F SIMS Instrument



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AIF CAMECA IMS-6F SIMS Facility



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SIMS Analysis Conditions

- CAMECA IMS-6F magnetic sector instrument
- Cs⁺ primary beam 6keV impact energy, 3nA
- Incidence angle 24° from normal
- 160µm x 160µm raster
- 30µm diameter detected area
- Mass resolution~500 (M/ΔM)
- Samples pumped to ~1x10⁻⁹ Torr before analysis
- Chamber pressure 2x10⁻¹⁰ Torr during analysis
- At least two sites measured per sample

Specimen Considerations

Samples submitted for analysis by Ganapati

- •Samples are 100, 110, 111 Nb from MaTecK •Float zone?
- Nb samples have a rough surface as received
- Roughness varies with sample
- Polycrystalline metals do not sputter uniformly but single crystal metals should

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Reflected light optical image



(100) as received

Profilometer roughness measurement: Peak-valley 0.6µm, RMS 0.13µ

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100 after 600C anneal (optical)



Peak-valley 1.0µm RMS 0.1µm

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Non-Annealed

111 100 110 QuickTime™ and a F (LZW) decompressor TIFE are needed to see this picture Nb100n2 raw Nb110n1 raw Nb111n1 raw 1E+07 1E+08 1E+07 1E+07 1E+06 1E+06 1E+06 1E+05 1E+05 Counts (cts/sec 1E+05 1E+04 1F+04 1E+04 1E+03 1E+03 1E+03 1E+02 1E+02 1E+02 1E+01 1E+01 1E+01 1E+00 1E+00 500 1000 0 1500 1E+00 0 500 1000 1500 500 1000 Time (s) Time (s) 0 Time (s) 110 and 111 were Au coated QuickTime[™] and a TIFF (LZW) decompressor are needed to see this picture as part of preparation for TEM analysis

Sputter rate ~0.5A/sec for analyses shown: 1000sec~50nm

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After 90C Anneal

110 111 (110 and 111 were Au coated)



Note H in 100 oxide

600sec~83nm

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100

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After 600C Anneal



(110 and 111 were Au coated)

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After 1250C Anneal



100 Nb sample: after 700nm, still in oxide

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100 Nb H/Nb Ratio



100 Nb O/Nb Ratio

1250 C annealed is heavily oxidized



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SIMS Results

- H, C, O detected and oxide present on all samples
- H after 90C anneal similar to un-annealed
 H higher in 100 oxide
- •H after 600C anneal lower than un-annealed
 - •H out diffuses
- After 1250C anneal, samples heavily oxidized
- No evidence of high oxygen content region below oxide
- C high at surface and then decreases for all samples

SIMS Summary and Future Work

- H, C, O can be analyzed in single crystal Nb
- Surface roughness limits depth resolution
- Some differences between crystal orientations
- 1250°C annealed samples heavily oxidized
- Need surface treatment to reduce surface roughness
- Need implant standards to quantify results



TEM Summary

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FIB Micromachining to Produce TEM Cross Sections



Called <u>lift-out</u> sample as final sample must be lifted out of the trench and mounted on a TEM grid. (or all material removed from TEM beam path)

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Lift-out methods are my favorite

- Foil(s) cut out from sample in FIB
- Foil(s) attached to TEM grid
 - Outside FIB (external)
 - Inside FIB (internal)
 - USING FIB INDUCED DEPOSITION





Locate areas, FIB thin and notch, attach needle, lift out and transfer



Why stop we only one or two samples?

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(100) after 600C anneal



Peak-valley 1.0µm RMS 0.1µm

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